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| INFORMATION DISCLOSURE CITATION <small>(List several items of citation)</small> | | | | | Berlin Number (Docket) PTO-92090571051 | Application Number 16/708,378 | |
| | | | | | Applicant(s) Bhu, et al. | Filing Date 2-27-04 | Group Art Unit 2618 |
| U.S. PATENT DOCUMENTS | | | | | | | |
| EXAMINER INITIAL | REF | DOCUMENT NUMBER | DATE | NAME | CLASS | SEARCH AREA | 16/708,378 11-3450-0001-00 |
| <i>W</i> | | 5,683,934 | 11-4-97 | Condalia | | | |
| | | 5,640,593 | 11-24-98 | Leedy | | | |
| | | 5,861,651 | 1-19-99 | Braves, et al. | | | |
| | | 5,880,040 | 3-9-99 | Sun, et al. | | | |
| <i>W</i> | | 5,940,716 | 8-17-99 | Jin, et al. | | | |
| U.S. PATENT APPLICATION PUBLICATIONS | | | | | | | |
| EXAMINER INITIAL | REF | DOCUMENT NUMBER | DATE | NAME | CLASS | SEARCH AREA | 16/708,378 11-3450-0001-00 |
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| FOREIGN PATENT DOCUMENTS | | | | | | | |
| | REF | DOCUMENT NUMBER | DATE | COUNTRY | CLASS | SEARCH AREA | SEARCH YEAR NO |
| | | | | | | | |
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| | | | | | | | |
| OTHER DOCUMENTS <small>(including Author, Date, Date, Patent Page, Etc.)</small> | | | | | | | |
| <i>W</i> | | S.R. Sheng, et al., "Degradation and Recovery of SiGe HBTs Following Radiation and Hot-Carrier Stressing." Pg. 14-15. Date is not available. | | | | | |
| <i>W</i> | | Z. Yang, et al., "Anodic Current Induced Hot Carrier Degradation in 100 GHz SiGe Heterojunction Bipolar Transistors." Pg. 1-8. Date is not available. | | | | | |
| EXAMINER: <i>Wynne</i> | | | | DATE CONSIDERED 2-15-05 | | | |
| EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP Section 609; Draw line through citation if not in conformance and not considered. Include copy of this form with any communication to applicant. | | | | | | | |

| INFORMATION DISCLOSURE CITATION <i>(Information disclosed (continued))</i> | | | | Document Number (Optional) 151920039971081 | Application Number 10/708,378 | | |
|---|-----|---|----------|---|----------------------------------|--------|------------------------------|
| | | | | Applicant(s) Bau, et al. | | | |
| | | | | Filing Date 2-27-04 | Group Art Unit 2618 | | |
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| U.S. PATENT DOCUMENTS | | | | | | | |
| EXAMINER INITIAL | REF | DOCUMENT NUMBER | DATE | NAME | CLASS | NUMBER | EXAMINER DEPARTMENT |
| PR | | 5,571,741 | 11-5-96 | Leedy | | | |
| | | 5,592,007 | 1-7-97 | Leedy | | | |
| | | 5,592,018 | 1-7-97 | Leedy | | | |
| | | 5,670,798 | 9-23-97 | Scheitzma | | | |
| WV | | 5,679,965 | 10-21-97 | Scheitzma | | | |
| U.S. PATENT APPLICATION PUBLICATIONS | | | | | | | |
| EXAMINER INITIAL | REF | DOCUMENT NUMBER | DATE | NAME | CLASS | NUMBER | FOUND RATE IF APPROPRIATE |
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| FOREIGN PATENT DOCUMENTS | | | | | | | |
| EXAMINER INITIAL | REF | DOCUMENT NUMBER | DATE | NAME | CLASS | NUMBER | TRANSLATE YES NO |
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| | | | | | | | |
| OTHER DOCUMENTS <i>(Including Author, Title, Date, Pertinent Page, etc.)</i> | | | | | | | |
| MJ | | H.S. Mermel, et al., "Temperature Dependence of Emitter-Base Reverse Stress Degradation and its Mechanism Analyzed by MOS Structures," Paper #2, pp. 146-147, IEEE, 1969 | | | | | |
| WV | | C.J. Huang, et al., "Temperature Dependence and Post-Stress Recovery of Hot Electron Degradation Effects in Bipolar Transistors," IEEE 1991 Bipolar Circuit and Technology Meeting #5, pp. 170-173. | | | | | |
| EXAMINER | | | | DATE CONSIDERED F-15-05 | | | |
| EXAMINER: Initial U denotes considered, whether or not citation is in conformance with MPEP Section 601; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant. | | | | | | | |